FAIRCHILD SEMICONDUCTOR®

March 2008

FDMC8462

N-Channel Power Trench® MOSFET

40V, 20A, 5.8mΩ

Features

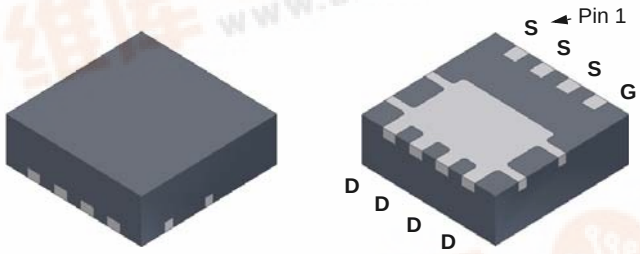
- Max $r_{DS(on)}$ = 5.8mΩ at V_{GS} = 10V, I_D = 13.5A
- Max $r_{DS(on)}$ = 8.0mΩ at V_{GS} = 4.5V, I_D = 11.8A
- Low Profile - 1mm max in Power 33
- 100% UIL Tested
- RoHS Compliant

General Description

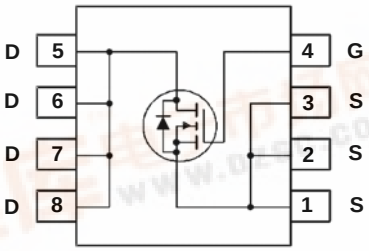
This N-Channel MOSFET is produced using Fairchild Semiconductor's advanced Power Trench® process that has been especially tailored to minimize the on-state resistance and yet maintain superior switching performance.

Application

- DC - DC Conversion



Power 33



MOSFET Maximum Ratings T_A = 25°C unless otherwise noted

Symbol	Parameter			Ratings	Units
V_{DS}	Drain to Source Voltage			40	V
V_{GS}	Gate to Source Voltage			±20	V
I_D	Drain Current -Continuous (Package limited)	T_C = 25°C		20	A
	-Continuous (Silicon limited)	T_C = 25°C		64	
	-Continuous	T_A = 25°C	(Note 1a)	14	
	-Pulsed			50	
E_{AS}	Single Pulse Avalanche Energy		(Note 3)	216	mJ
P_D	Power Dissipation	T_C = 25°C		41	W
	Power Dissipation	T_A = 25°C	(Note 1a)	2.0	
T_J, T_{STG}	Operating and Storage Junction Temperature Range			-55 to +150	°C

Thermal Characteristics

$R_{\theta JC}$	Thermal Resistance, Junction to Case	3	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient (Note 1a)	53	

Package Marking and Ordering Information

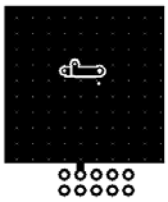
Device Marking	Device	Package	Reel Size	Tape Width	Quantity
FDMC8462	FDMC8462	Power 33	13"	12mm	3000 units

Electrical Characteristics T_J = 25°C unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
Off Characteristics						
BV_{DSS}	Drain to Source Breakdown Voltage	I_D = 250μA, V_{GS} = 0V	40			V
$\frac{\Delta BV_{DSS}}{\Delta T_J}$	Breakdown Voltage Temperature Coefficient	I_D = 250μA, referenced to 25°C		31		mV/°C
I_{DSS}	Zero Gate Voltage Drain Current	V_{GS} = 0V, V_{DS} = 32V,			1	μA
I_{GSS}	Gate to Source Leakage Current	V_{GS} = ±20V, V_{DS} = 0V			±100	nA
On Characteristics						
$V_{GS(th)}$	Gate to Source Threshold Voltage	V_{GS} = V_{DS}, I_D = 250μA	1.0	2.0	3.0	V
$\frac{\Delta V_{GS(th)}}{\Delta T_J}$	Gate to Source Threshold Voltage Temperature Coefficient	I_D = 250μA, referenced to 25°C		-6.6		mV/°C
$r_{DS(on)}$	Static Drain to Source On Resistance	V_{GS} = 10V, I_D = 13.5A		4.7	5.8	mΩ
		V_{GS} = 4.5V, I_D = 11.8A		6.4	8.0	
		V_{GS} = 10V, I_D = 13.5A, T_J = 125°C		7.1	9.3	
g_{FS}	Forward Transconductance	V_{DD} = 5V, I_D = 13.5A		60		S
Dynamic Characteristics						
C_{iss}	Input Capacitance	V_{DS} = 20V, V_{GS} = 0V, f = 1MHz		2000	2660	pF
C_{oss}	Output Capacitance			545	725	pF
C_{rss}	Reverse Transfer Capacitance			80	120	pF
R_g	Gate Resistance	f = 1MHz		2.7		Ω
Switching Characteristics						
$t_{d(on)}$	Turn-On Delay Time	V_{DD} = 20V, I_D = 13.5A, V_{GS} = 10V, R_{GEN} = 6Ω		12	21	ns
t_r	Rise Time			4	10	ns
$t_{d(off)}$	Turn-Off Delay Time			27	43	ns
t_f	Fall Time			3	10	ns
Q_g	Total Gate Charge	V_{GS} = 0V to 10V; V_{DD} = 20V, I_D = 13.5A		30	43	nC
Q_g	Total Gate Charge	V_{GS} = 0V to 4.5V; V_{DD} = 20V, I_D = 13.5A		15	21	nC
Q_{gs}	Gate to Source Charge	V_{DD} = 20V, I_D = 13.5A		6		nC
Q_{gd}	Gate to Drain “Miller” Charge	V_{DD} = 20V, I_D = 13.5A		5		nC
Drain-Source Diode Characteristics						
V_{SD}	Source to Drain Diode Forward Voltage	V_{GS} = 0V, I_S = 13.5A (Note 2)		0.8	1.3	V
		V_{GS} = 0V, I_S = 1.7A (Note 2)		0.7	1.2	
t_{rr}	Reverse Recovery Time	I_F = 13.5A, di/dt = 100A/μs		35	57	ns
Q_{rr}	Reverse Recovery Charge			20	32	nC

NOTES:

1. $R_{\theta JA}$ is determined with the device mounted on a 1in^2 pad 2 oz copper pad on a 1.5 x 1.5 in. board of FR-4 material. $R_{\theta JC}$ is guaranteed by design while $R_{\theta CA}$ is determined by the user's board design.



a. 53°C/W when mounted on a 1 in^2 pad of 2 oz copper

b. 125°C/W when mounted on a minimum pad of 2 oz copper

2. Pulse Test: Pulse Width < 300μs, Duty cycle < 2.0%.

3. Starting T_J = 25°C; N-ch: L = 3 mH, I_{AS} = 12A, V_{DD} = 40V, V_{GS} = 10V

Typical Characteristics T_J = 25°C unless otherwise noted

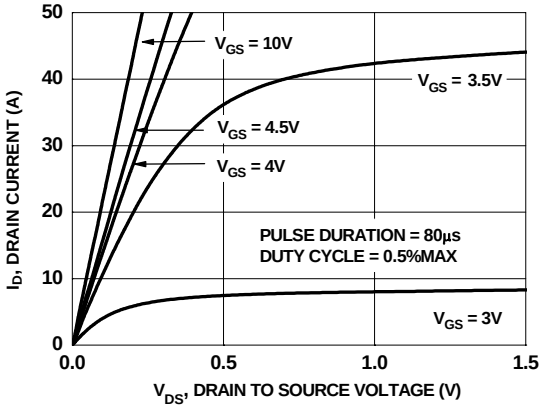


Figure 1. On-Region Characteristics

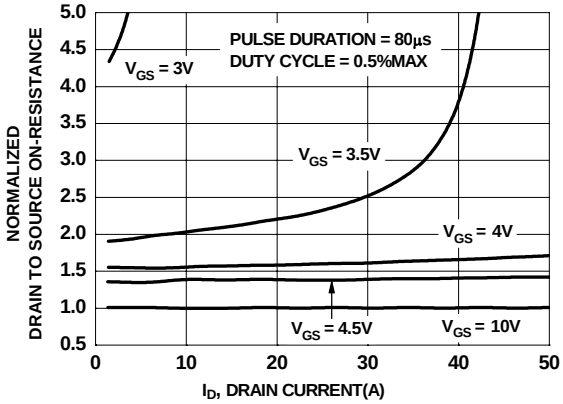


Figure 2. Normalized On-Resistance vs Drain Current and Gate Voltage

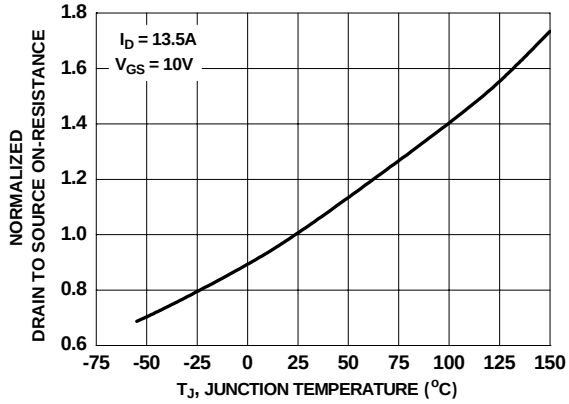


Figure 3. Normalized On-Resistance vs Junction Temperature

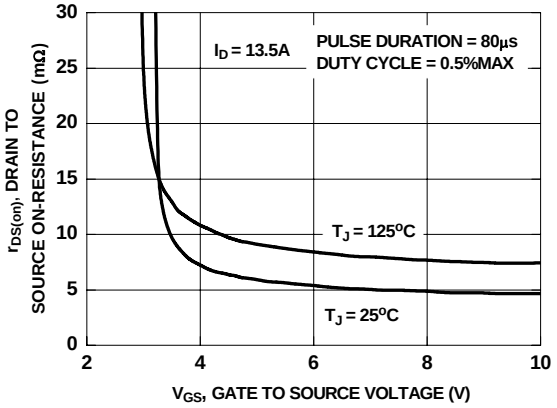


Figure 4. On-Resistance vs Gate to Source Voltage

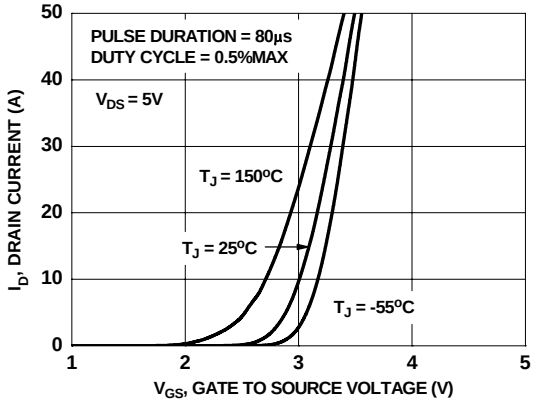


Figure 5. Transfer Characteristics

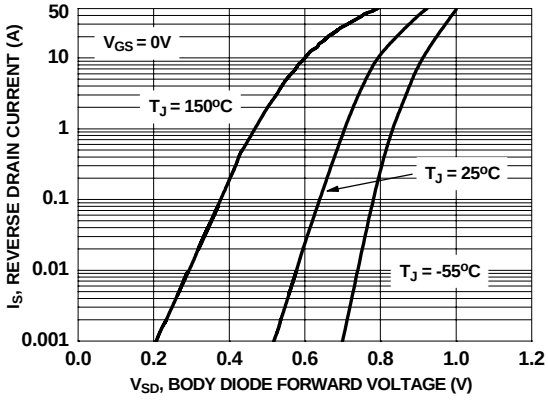


Figure 6. Source to Drain Diode Forward Voltage vs Source Current

Typical Characteristics T_J = 25°C unless otherwise noted

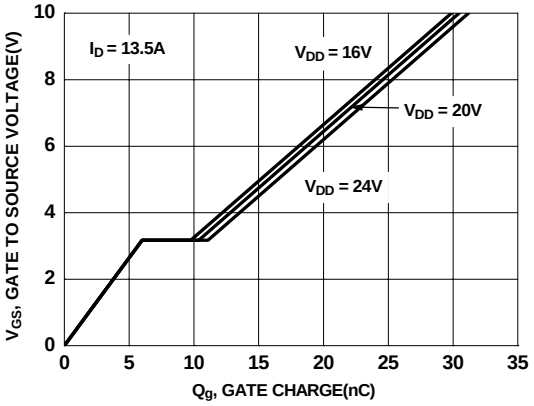


Figure 7. Gate Charge Characteristics

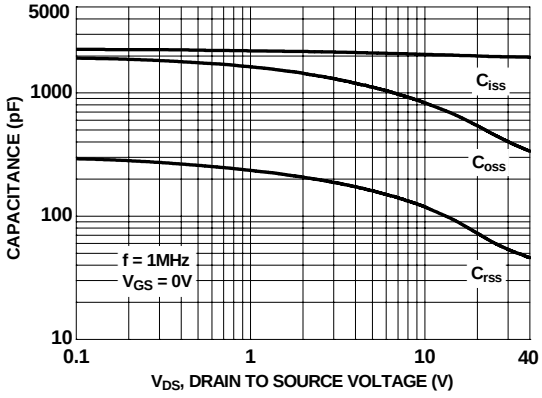


Figure 8. Capacitance vs Drain to Source Voltage

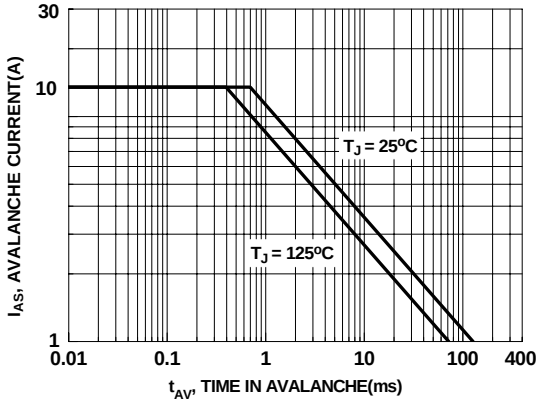


Figure 9. Unclamped Inductive Switching Capability

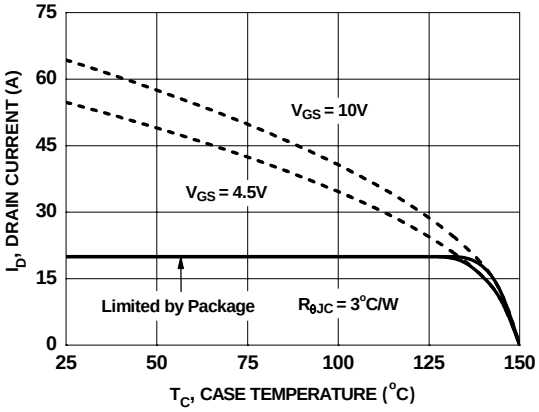


Figure 10. Maximum Continuous Drain Current vs Case Temperature

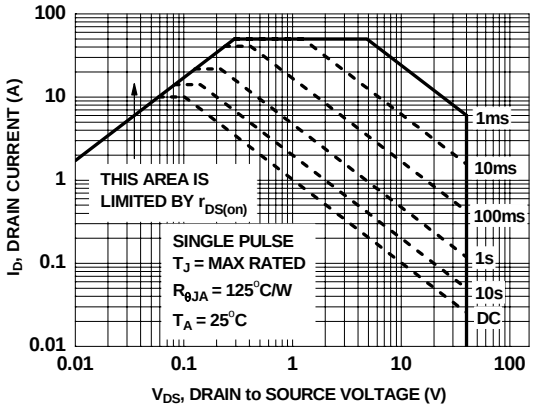


Figure 11. Forward Bias Safe Operating Area

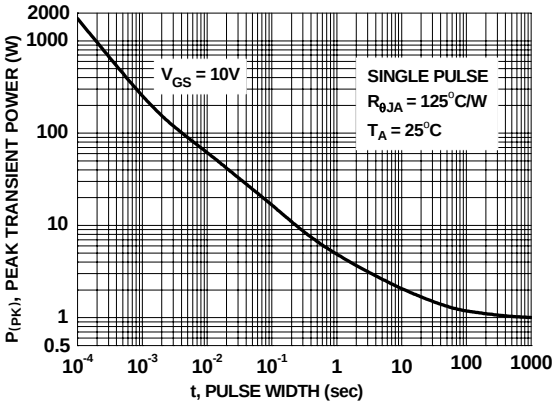


Figure 12. Single Pulse Maximum Power Dissipation

Typical Characteristics T_J = 25°C unless otherwise noted

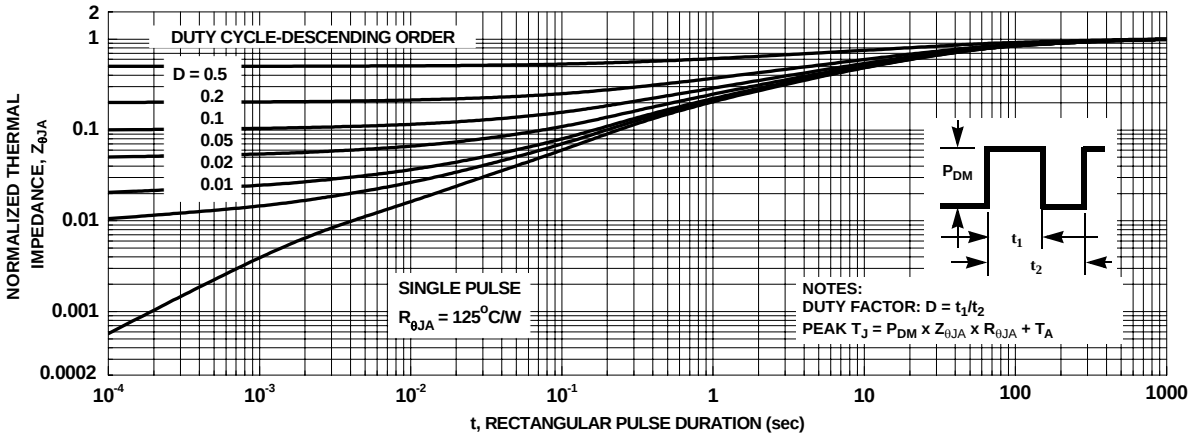
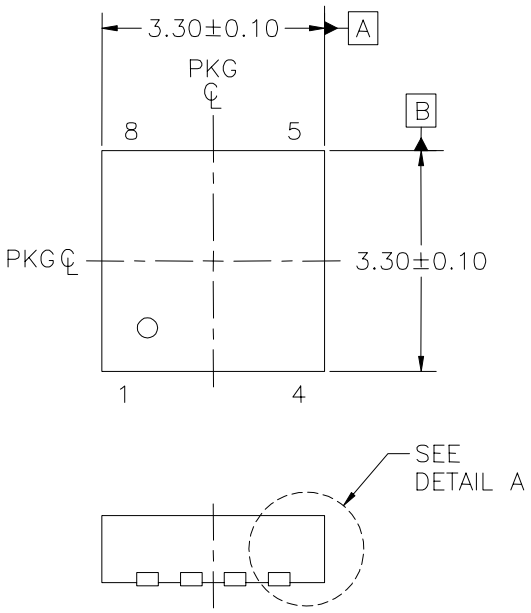
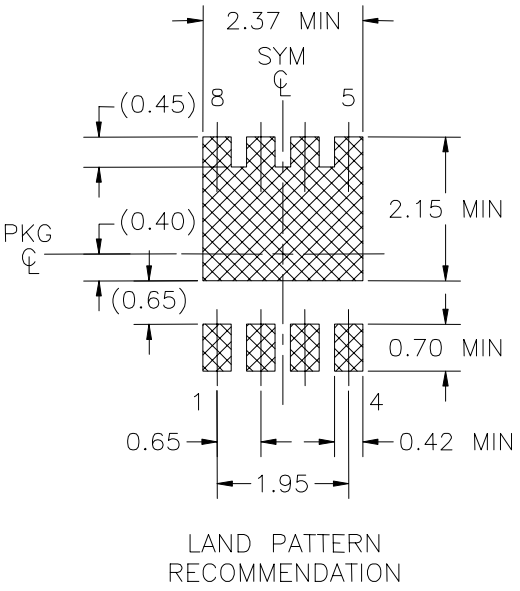


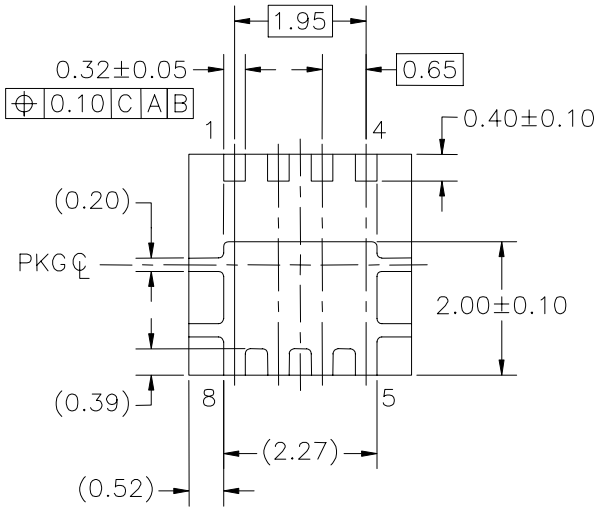
Figure 13. Transient Thermal Response Curve

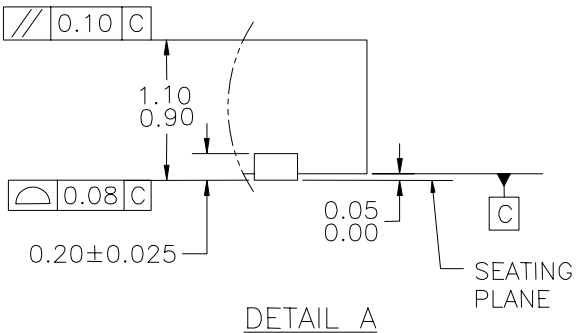
Dimensional Outline and Pad Layout





LAND PATTERN
RECOMMENDATION





DETAIL A
SCALE: 2X

NOTES: UNLESS OTHERWISE SPECIFIED

A) PACKAGE STANDARD REFERENCE: JEDEC MO-240, ISSUE A, VAR. BA, DATED OCTOBER 2002.
B) ALL DIMENSIONS ARE IN MILLIMETERS.
C) DIMENSIONS DO NOT INCLUDE BURRS OR MOLD FLASH. MOLD FLASH OR BURRS DOES NOT EXCEED 0.10MM.
D) DIMENSIONING AND TOLERANCING PER ASME Y14.5M-1994.
E) DRAWING FILE NAME: PQFN08BREV1

PQFN08BREV1

FAIRCHILD SEMICONDUCTOR®

TRADEMARKS

The following includes registered and unregistered trademarks and service marks, owned by Fairchild Semiconductor and/or its global subsidianries, and is not intended to be an exhaustive list of all such trademarks.

ACEx®
Build it Now™
CorePLUS™
CorePOWER™
CROSSVOLT™
CTL™
Current Transfer Logic™
EcoSPARK®
EfficentMax™
EZSWITCH™ *
™
®
Fairchild®
Fairchild Semiconductor®
FACT Quiet Series™
FACT®
FAST®
FastvCore™
FlashWriter® *
FPS™
F-PFS™
FRFET®
Global Power Resource℠
Green FPS™
Green FPS™ e-Series™
GTO™
IntelliMAX™
ISOPLANAR™
MegaBuck™
MICROCOUPLER™
MicroFET™
MicroPak™
MillerDrive™
MotionMax™
Motion-SPM™
OPTOLOGIC®
OPTOPLANAR®
®
PDP-SPM™
Power-SPM™
PowerTrench®
Programmable Active Droop™
QFET®
QS™
Quiet Series™
RapidConfigure™
Saving our world 1mW at a time™
SmartMax™
SMART START™
SPM®
STEALTH™
SuperFET™
SuperSOT™-3
SuperSOT™-6
SuperSOT™-8
SuperMOS™
SYSTEM GENERAL ®
The Power Franchise®
the power franchise
TinyBoost™
TinyBuck™
TinyLogic®
TINYOPTO™
TinyPower™
TinyPWM™
TinyWire™
µSerDes™
µ SerDes™
UHC®
Ultra FRFET™
UniFET™
VCX™
VisualMax™

* EZSWITCH™ and FlashWriter® are trademarks of System General Corporation, used under license by Fairchild Semiconductor.

DISCLAIMER

FAIRCHILD SEMICONDUCTOR RESERVES THE RIGHT TO MAKE CHANGES WITHOUT FURTHER NOTICE TO ANY PRODUCTS HEREIN TO IMPROVE RELIABILITY, FUNCTION, OR DESIGN. FAIRCHILD DOES NOT ASSUME ANY LIABILITY ARISING OUT OF THE APPLICATION OR USE OF ANY PRODUCT OR CIRCUIT DESCRIBED HEREIN; NEITHER DOES IT CONVEY ANY LICENSE UNDER ITS PATENT RIGHTS, NOR THE RIGHTS OF OTHERS. THESE SPECIFICATIONS DO NOT EXPAND THE TERMS OF FAIRCHILD'S WORLDWIDE TERMS AND CONDITIONS, SPECIFICALLY THE WARRANTY THEREIN, WHICH COVERS THESE PRODUCTS.

LIFE SUPPORT POLICY

FAIRCHILD'S PRODUCTS ARE NOT AUTHORIZED FOR USE AS CRITICAL COMPONENTS IN LIFE SUPPORT DEVICES OR SYSTEMS WITHOUT THE EXPRESS WRITTEN APPROVAL OF FAIRCHILD SEMICONDUCTOR CORPORATION.

As used herein:

1. Life support devices or systems are devices or systems which, (a) are intended for surgical implant into the body or (b) support or sustain life, and (c) whose failure to perform when properly used in accordance with instructions for use provided in the labeling, can be reasonably expected to result in a significant injury of the user.
2. A critical component in any component of a life support, device, or system whose failure to perform can be reasonably expected to cause the failure of the life support device or system, or to affect its safety or effectiveness.

PRODUCT STATUS DEFINITIONS

Definition of Terms

Datasheet Identification	Product Status	Definition
Advance Information	Formative or In Design	This datasheet contains the design specifications for product development. Specifications may change in any manner without notice.
Preliminary	First Production	This datasheet contains preliminary data; supplementary data will be published at a later date. Fairchild Semiconductor reserves the right to make changes at any time without notice to improve design.
No Identification Needed	Full Production	This datasheet contains final specifications. Fairchild Semiconductor reserves the right to make changes at any time without notice to improve the design.
Obsolete	Not In Production	This datasheet contains specifications on a product that is discontinued by Fairchild Semiconductor. The datasheet is for reference information only.

Rev. I34